What is claimed is:

1. A magnetoresistance memory comprising:

a memory cell storing information;

a conductive line contacting the memory cell to change the magnetization direction of the memory cell by generating a magnetic field; and

at least one flux concentrating island located between the conductive line and the memory cell for concentrating flux onto the memory cell.

2. The memory of claim 1, wherein the conductive line is a bit line or a digit line which is formed to cross the bit line at a right angle while interposing the memory cell between the bit line and the digit line.

3. The memory of claim 1, wherein the conductive line includes a flux concentration layer for concentrating the flux onto the memory cell on a surface which does not contact the memory cell.

4. The memory of claim 1, wherein the flux concentrating island is formed using a material having high permeability.

5. The memory of claim 1, wherein the flux concentrating layer is formed using a material having high permeability.

6. The memory of claim 1, wherein the flux concentrating island improves selectivity by 5% or more.

7. A method of manufacturing a magnetoresistance memory comprising:

forming a memory cell and a conductive line by applying electric current to the memory cell on a substrate; and

forming a flux concentrating island, which concentrates flux onto the memory cell, between the memory cell and the conductive line.

8. The method of claim 7, wherein the conductive line is a bit line or a digit line which is formed to cross the bit line at a right angle while interposing the memory cell between the bit line and the digit line.

9. The method of claim 7, further comprising forming a flux concentration layer concentrating the flux onto the memory cell on a surface which does not contact the memory cell.

10. The method of claim 7, wherein the flux concentrating island is formed using a material having high permeability.

11. The method of claim 9, wherein the flux concentration layer is formed using a material having high permeability.

12. The method of claim 7, wherein the flux concentrating island improves the selectivity by 5% or more.